

20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C		
-20V	1.9Ω @ V _{GS} = -4.5V	-0.53A		
	2.4Ω @ V _{GS} = -2.5V	-0.46A		
	3.4Ω @ V _{GS} = -1.8V	-0.38A		
	5.0Ω @ V _{GS} = -1.5V	-0.31A		

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- **Power Management Functions**
- Analog Switch

Features and Benefits

- Low Package Profile
- 0.6mm × 0.4mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage: -1.0V Max
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

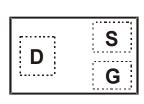
- Case: X2-DFN0604-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.001 grams (Approximate)

X2-DFN0604-3

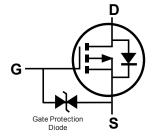








Top View Package Pin Configuration



Equivalent Circuit

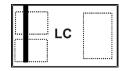
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP22D5UFO-7B	X2-DFN0604-3	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



Top View Bar Denotes Gate and Source Side

LC = Product Type Marking Code



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	T _A = +25°C T _A = +85°C	I _D	-0.53 -0.38	А
Pulsed Drain Current (Note 6)			I _{DM}	-0.6	Α

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P _D	0.77	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	163	°C/W
Total Power Dissipation (Note 6)	Steady State	P _D	0.34	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	368	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

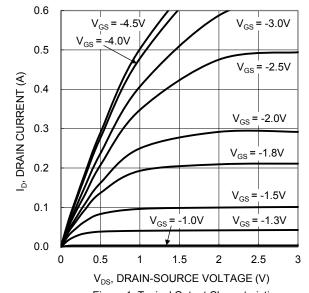
Electrical Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	, <u>-</u>			I			
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_		V	V _{GS} = 0V, I _D = -250μA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	V _{DS} = -16V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						•	
Gate Threshold Voltage	V _{GS(TH)}	-0.4	_	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA	
		_	0.95	1.9		$V_{GS} = -4.5V, I_D = -100mA$	
Static Drain-Source On-Resistance	D- avavii [_	1.2	2.4	Ω	$V_{GS} = -2.5V, I_D = -50mA$	
Static Dialit-Source Off-Nesistance	R _{DS(ON)}	_	1.4	3.4	1 11	$V_{GS} = -1.8V$, $I_D = -20mA$	
		_	1.7	5.0		$V_{GS} = -1.5V, I_D = -10mA$	
Diode Forward Voltage	V_{SD}	_	-0.5	-1.1	V	$V_{GS} = 0V, I_{S} = -10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	17	_	pF	.,	
Output Capacitance	Coss	_	4.1	_	pF	$V_{DS} = -16V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	2.7	_	pF	1 - 1.0WHZ	
Gate Resistance	R _g	_	3.3	_	kΩ	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Qg	_	0.3	_	nC	15)()(40)(
Gate-Source Charge	Q _{gs}	_	0.04	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -250$ mA	
Gate-Drain Charge	Q_{gd}	_	0.1	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	7.3	_	ns		
Turn-On Rise Time	t _R	_	20.7	_	ns	V _{DD} = -15V, V _{GS} = -4.5V,	
Turn-Off Delay Time	t _{D(OFF)}		185		ns	$R_G = 2\Omega$, $I_D = -200 \text{mA}$	
Turn-Off Fall Time	t _F	_	97	_	ns		

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. 10µs pulse duty cycle = 1%. 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.





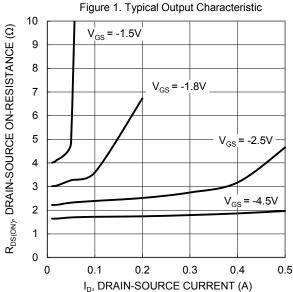


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

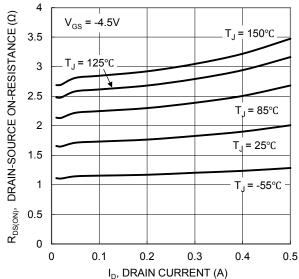


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

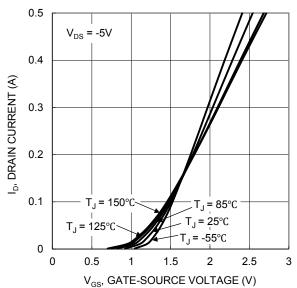


Figure 2. Typical Transfer Characteristic

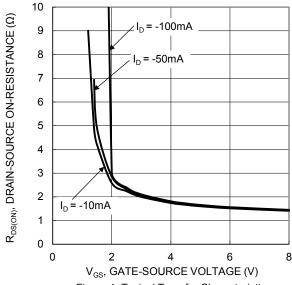


Figure 4. Typical Transfer Characteristic

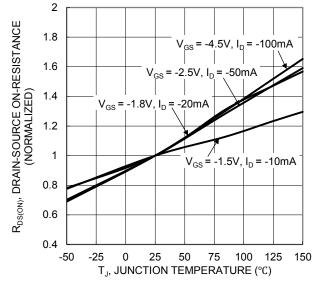


Figure 6. On-Resistance Variation with Junction Temperature



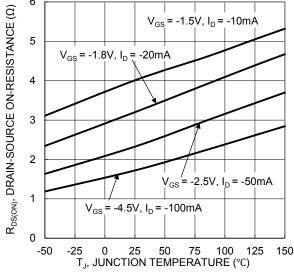
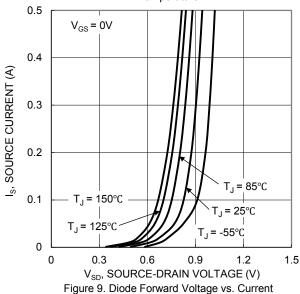
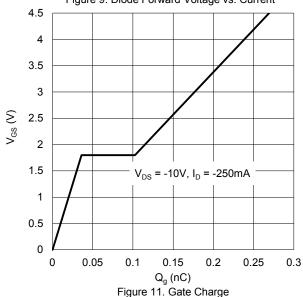


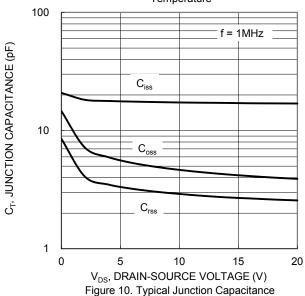
Figure 7. On-Resistance Variation with Junction Temperature





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Figure 8. Gate Threshold Variation vs. Junction Temperature



1 R_{DS(ON)} Limited ID, DRAIN CURRENT (A) 0.1 $P_W = 10s$ 0.01 T_{J(Max)} = 150 ℃ DC T_C = 25°C Single Pulse DUT on 1*MRP Board $V_{GS} = -4.5V$ 0.001 0.1 10 100

 $V_{\rm DS}$, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



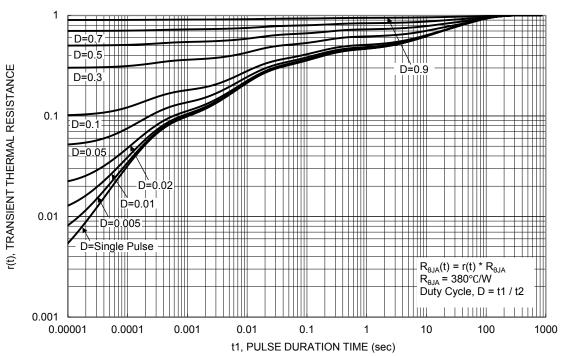
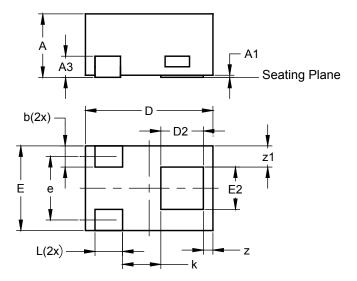


Figure 13. Transient Thermal Resistance



Package Outline Dimensions

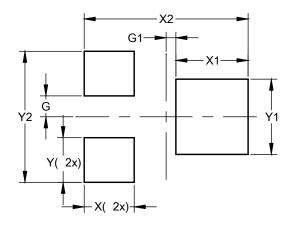
Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN0604-3					
Dim	Min	Max	Тур		
Α		0.40	0.36		
A1	0.00	0.03	0.02		
A3			0.10		
b	0.07	0.15	0.10		
D	0.55	0.65	0.60		
D2	0.15	0.25	0.20		
Е	0.35	0.45	0.40		
E2	0.15	0.25	0.20		
е	-	1	0.30		
k	0.15	1			
L	0.10	0.18	0.13		
Z			0.045		
z1			0.10		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
G	0.075		
G1	0.035		
X	0.180		
X1	0.260		
X2	0.590		
Υ	0.160		
Y1	0.270		
Y2	0.470		



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